Preferred Device

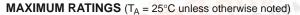
Power MOSFET 200 mA, 50 V

N-Channel SOT-23

Typical applications are DC–DC converters, power management in portable and battery–powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

- Pb–Free Packages are Available
- Low Threshold Voltage (V_{GS(th)}: 0.5 V-1.5 V) Makes it Ideal for Low Voltage Applications
- Miniature SOT-23 Surface Mount Package Saves Board Space



Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	50	Vdc
Gate-to-Source Voltage - Continuous	V_{GS}	± 20	Vdc
Drain Current - Continuous @ T _A = 25°C - Pulsed Drain Current (t _p ≤ 10 μs)	I _D I _{DM}	200 800	mA
Total Power Dissipation @ T _A = 25°C	P _D	225	mW
Operating and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Thermal Resistance – Junction–to–Ambient	R _{θJA}	556	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	D-TL	260	°C

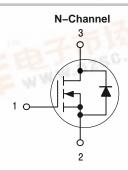
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



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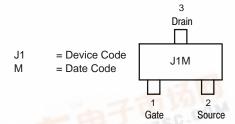
200 mA, 50 V $R_{DS(on)} = 3.5 Ω$





SOT-23 CASE 318 STYLE 21

MARKING DIAGRAM & PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping [†]
BSS138LT1	SOT-23	3000 Tape & Reel
BSS138LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
BSS138LT3	SOT-23	10,000 Tape & Reel
BSS138LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



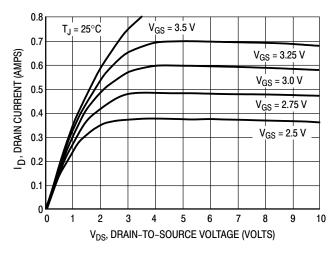
Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic			Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 250 μAdc)			50	_	-	Vdc
Zero Gate Voltage Drain Current $(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0 \text{ Vdc})$ $(V_{DS} = 50 \text{ Vdc}, V_{GS} = 0 \text{ Vdc})$		I _{DSS}	_ _	- -	0.1 0.5	μAdc
Gate–Source Leakage Current ($V_{GS} = \pm 20 \text{ Vdc}$, $V_{DS} = 0 \text{ Vdc}$)			_	-	±0.1	μAdc
ON CHARACTERISTICS (Note 1)						
Gate–Source Threshold Voltage $(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$		V _{GS(th)}	0.5	_	1.5	Vdc
Static Drain–to–Source On–Resistance $ \begin{array}{l} (V_{GS}=2.75~Vdc,~I_D<200~mAdc,~T_A=-40^{\circ}C~to~+85^{\circ}C)\\ (V_{GS}=5.0~Vdc,~I_D=200~mAdc) \end{array} $		r _{DS(on)}	_ _	5.6 -	10 3.5	Ohms
Forward Transconductance (V _{DS} = 25 Vdc, I _D = 200 mAdc, f = 1.0 kHz)		9 _{fs}	100	_	-	mmhos
DYNAMIC CHARACTERISTICS		•		•		•
Input Capacitance	$(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ MHz})$	C _{iss}	_	40	50	pF
Output Capacitance	$(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ MHz})$	C _{oss}	-	12	25	
Transfer Capacitance	$(V_{DG} = 25 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ MHz})$	C _{rss}	_	3.5	5.0	
SWITCHING CHARACTERISTICS (N	ote 2)					
Turn-On Delay Time	(V 20)/da 0.0 A da)	t _{d(on)}	_	-	20	ns
Turn-Off Delay Time	$(V_{DD} = 30 \text{ Vdc}, I_D = 0.2 \text{ Adc},)$	t _{d(off)}	-	-	20	

Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperature.

TYPICAL ELECTRICAL CHARACTERISTICS



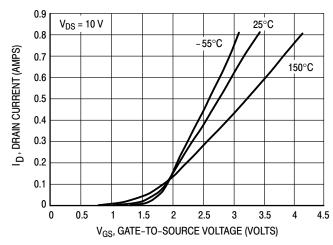
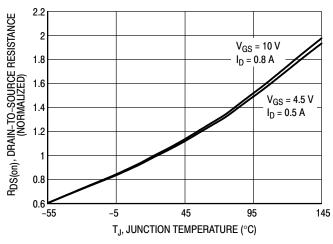


Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



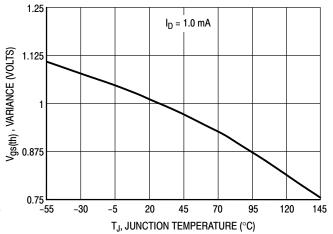


Figure 3. On–Resistance Variation with Temperature

Figure 4. Threshold Voltage Variation with Temperature

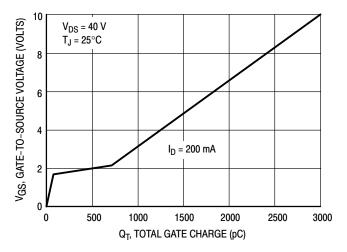
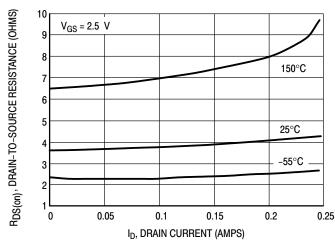


Figure 5. Gate Charge

TYPICAL ELECTRICAL CHARACTERISTICS



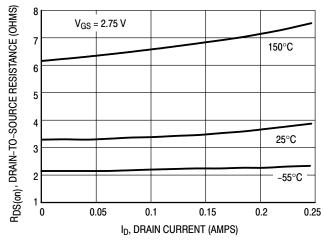
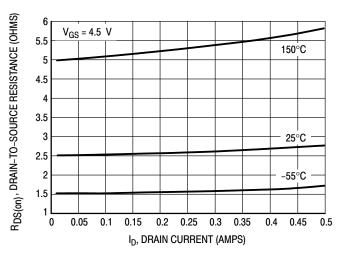


Figure 6. On-Resistance versus Drain Current

Figure 7. On-Resistance versus Drain Current



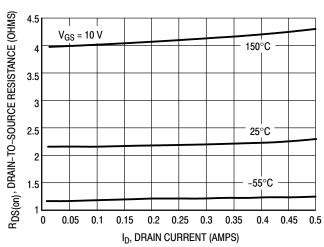
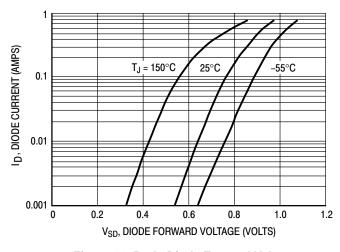


Figure 8. On-Resistance versus Drain Current

Figure 9. On-Resistance versus Drain Current



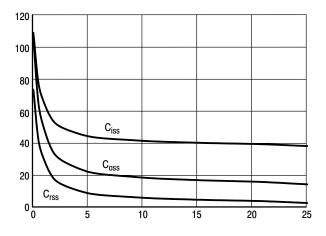
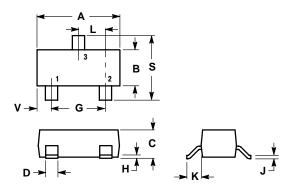


Figure 10. Body Diode Forward Voltage

Figure 11. Capacitance

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AH**



- DTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL

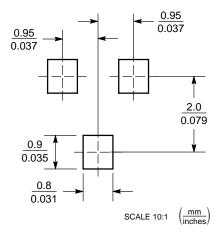
 4. 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.1102	0.1197	2.80	3.04
В	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
Н	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
v	0.0177	0.0236	0.45	0.60

STYLE 21: PIN 1. GATE 2. SOURG 3. DRAIN

- SOURCE DRAIN

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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